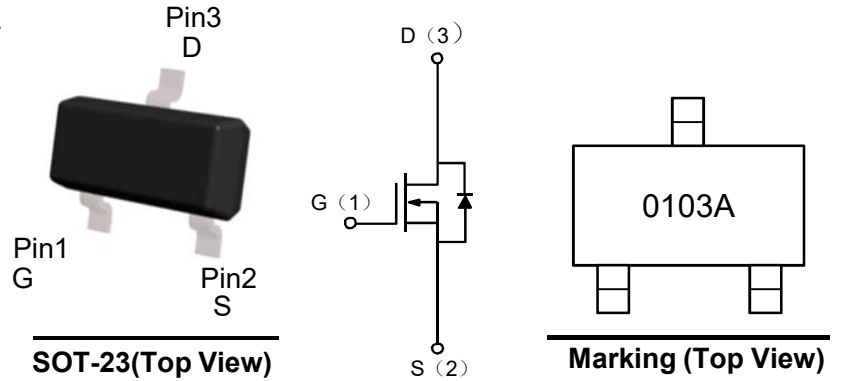


**Description**

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

**MOSFET Product Summary**

$V_{DS}(V)$	$R_{DS(on)}(\Omega)$	$I_D(A)$
100	0.23@ VGS=10V	2

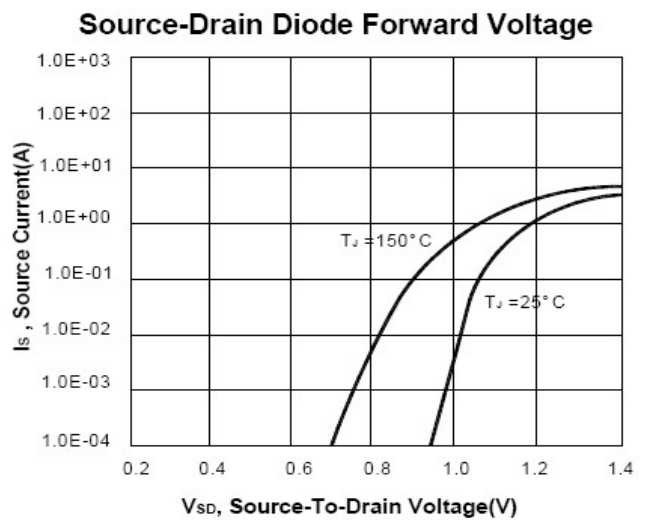
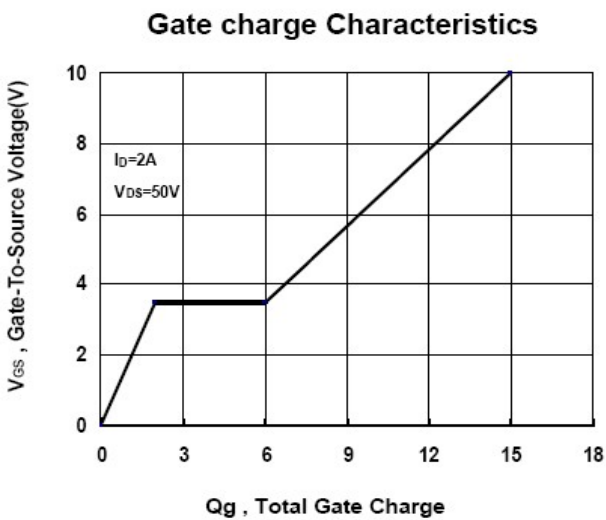
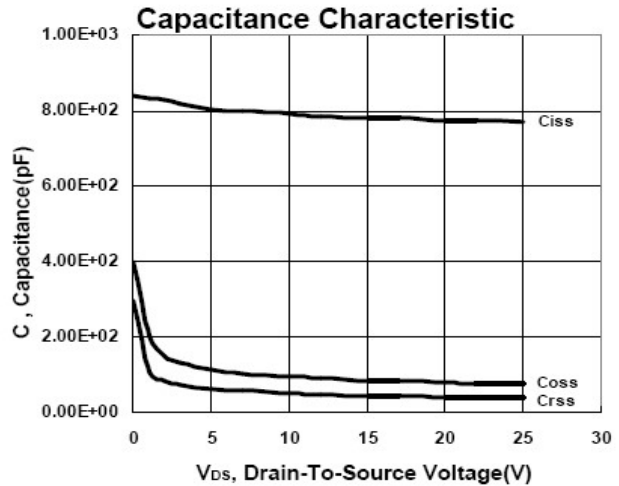
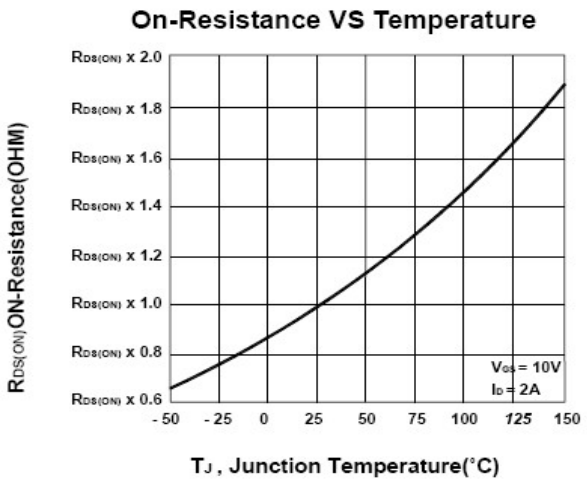
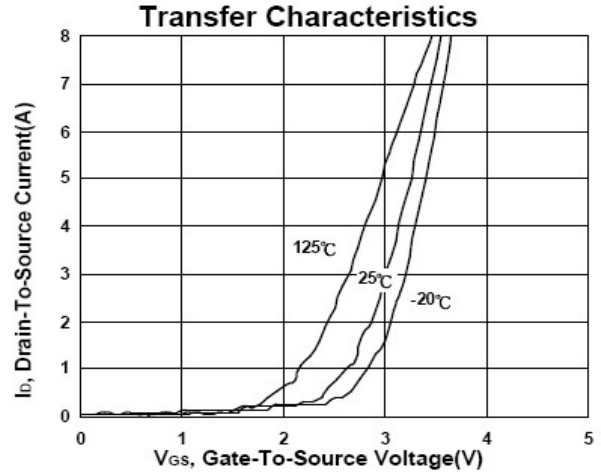
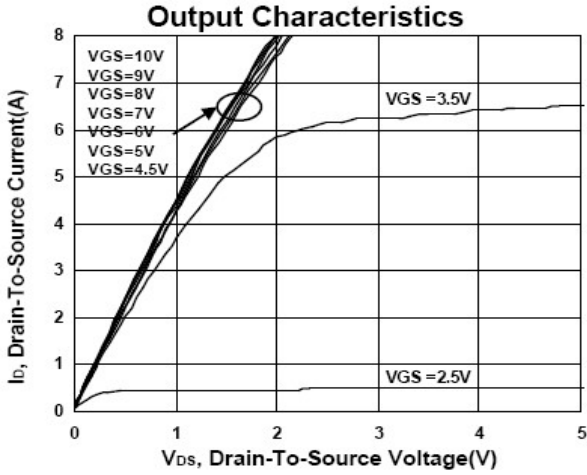

**Absolute maximum rating@25°C**

Parameter		Symbol	Value	Units
Drain-Source Voltage		$V_{DS}$	100	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current	$T_A=25^\circ C$	$I_D$	2	A
	$T_A=70^\circ C$		0.8	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	18	A
Avalanche Current		$I_{AS}$	18	A
Avalanche Energy	L=0.1mH	EAS	16.5	mJ
Maximum Power Dissipation	$T_A=25^\circ C$	$P_D$	0.75	W
	$T_A=70^\circ C$		0.3	
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 to 150	°C
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	166	°C/W

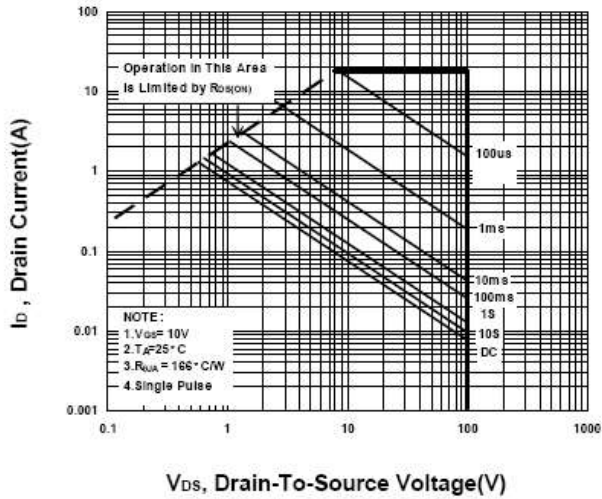
**Electrical characteristics per line@25°C ( unless otherwise specified)**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>OFF/ON CHARACTERISTICS</b>						
<b>STATIC PARAMETERS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu A, V_{GS} = 0V$	100		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 80V, V_{GS} = 0V$	-	-	1	$\mu A$
		$V_{DS} = 80V, V_{GS} = 0V$ $V_{Tj} = 1255^\circ C$			10	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.5	2.0	V
On-State Drain Current <sup>1</sup>	$I_{D(ON)}$	$V_{DS} = 10V, V_{GS} = 10V$	18			A
Drain-Source On- Static Resistance <sup>1</sup>	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 2A$	-	0.2	0.23	$\Omega$
		$V_{GS} = 5V, I_D = 1A$	-	0.22	0.25	$\Omega$
Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = 10V, I_D = 2A$		10		S
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	$C_{ISS}$	$V_{GS} = 0V, V_{DS} = 25V,$ $f = 1MHz$	-	800		pF
Output Capacitance	$C_{OSS}$		-	80		pF
Reverse Transfer Capacitance	$C_{RSS}$		-	40		pF
Gate Resistance	$R_g$	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		2.5		$\Omega$
Total Gate Charge <sup>2</sup>	$Q_g$	$V_{DS} = 50V, V_{GS} = 10V,$ $I_D = 2A$		15		nC
Gate-Source Charge <sup>2</sup>	$Q_{gs}$			2		
Gate-Drain Charge <sup>2</sup>	$Q_{gd}$			4		
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$	$V_{DD} = 50V, I_D @ 2A, V_{GS} = 10V,$ $R_{GS} = 6\Omega$		16		nS
Rise Time <sup>2</sup>	$t_r$			330		
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$			39		
Fall Time <sup>2</sup>	$t_f$			111		
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTIC ( <math>T_J = 25^\circ C</math> )</b>						
Continuous Current	$I_S$				10	A
Forward Voltage <sup>1</sup>	$V_{SD}$	$I_F = 2A, V_{GS} = 0V$			1.4	V
Reverse Recovery Time	$t_{rr}$	$I_F = 2A, di/dt = 500A/\mu S$		75		nS
Reverse Recovery Charge	$Q_{rr}$			0.17		nC

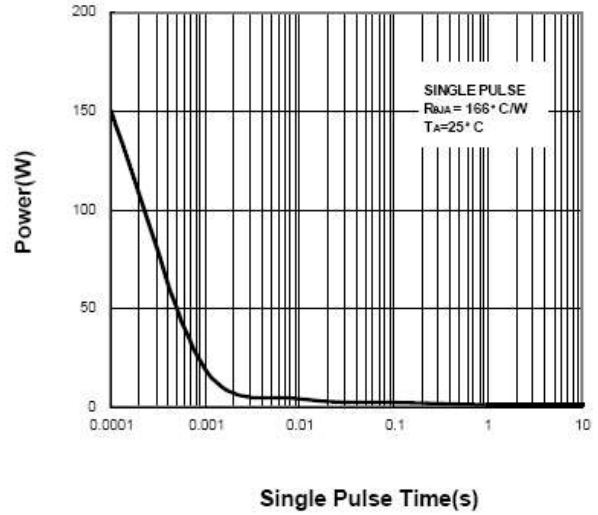
Typical Characteristics



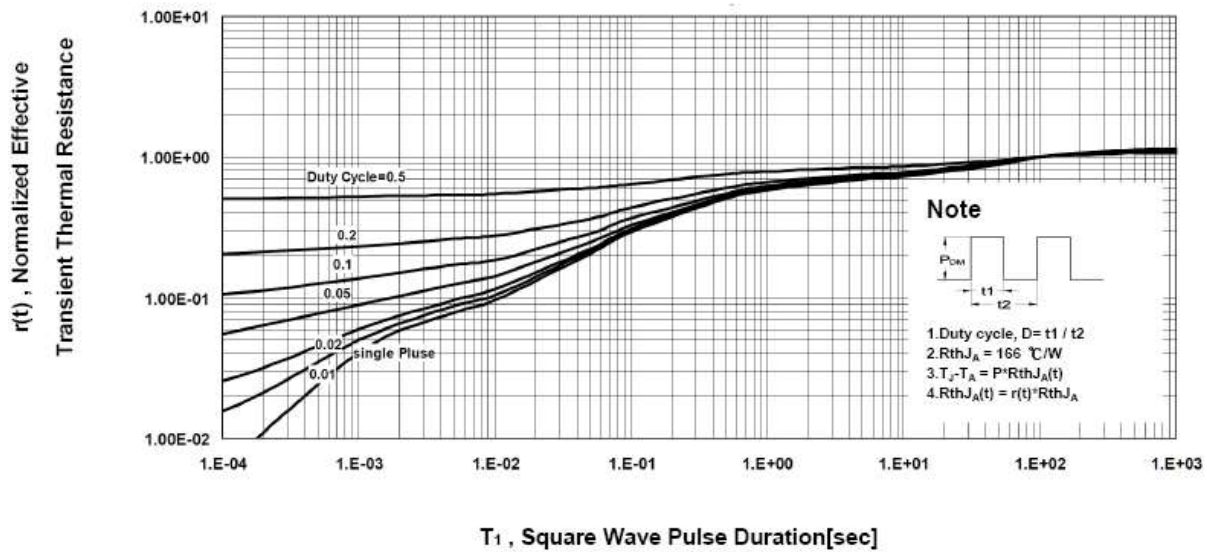
Safe Operating Area



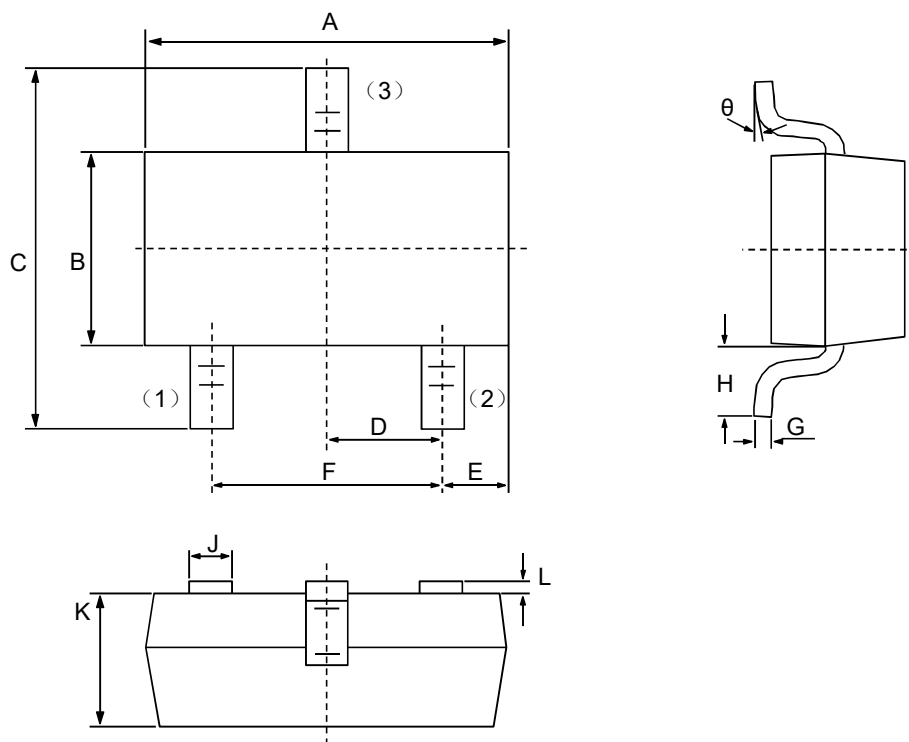
Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve




Product dimension(SOT-23)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.80	3.00	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	2.10	2.50	0.0830	0.0984
D	0.89	1.02	0.0350	0.0401
E	0.45	0.60	0.0177	0.0236
F	1.78	2.04	0.0701	0.0807
G	0.085	0.177	0.0034	0.0070
H	0.45	0.60	0.0180	0.0236
J	0.37	0.50	0.0150	0.0200
K	0.89	1.11	0.0350	0.0440
L	0.013	0.100	0.0005	0.0040
θ	0°	10°	0°	10°


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